

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT APPLICATION

Huili Shao Allen Yen Susan Clay Vitkavage

CASE

1-10-3

Serial No.

09/464811

Group Art Unit

2815

Filed

December 17, 1999

Examiner

L. Cruz

Title

Integration Of Low Dielectric Material In Semiconductor Circuit Structures

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

Enclosed is an amendment in the above-identified application.

NO ADDITIONAL FEE REQUIRED

In the event of non-payment or improper payment of a required fee, the Commissioner is authorized to charge or to credit Deposit Account No. 12-2325 as required to correct the error.

Respectfully,

Anthony Grillo, Attorney

Reg. No. 36535 610-712-3766.

Lucent Technologies Inc.

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P.O. Box 636

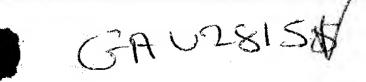
Murray Hill, New Jersey 07974-0636

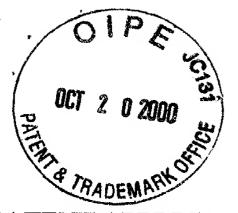
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AMENDMENT

In response to the Office Action mailed May 17, 2000, please amend the above-identified application as follows:

IN THE SPECIFICATION

✓Page 7, line 31: change "2500" to -- 250 --.

Page 8, line 19: after "dielectric layer" delete "350".

IN THE CLAIMS

1(Amended). A semiconductor structure comprising:

a first upper level of interconnect members formed over a semiconductor layer having an electronic device formed thereon;

at least one lower level of interconnect members formed between the semiconductor layer and the first upper level;

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